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Local and Direct EM Injection of Power into CMOS Integrated Circuits.

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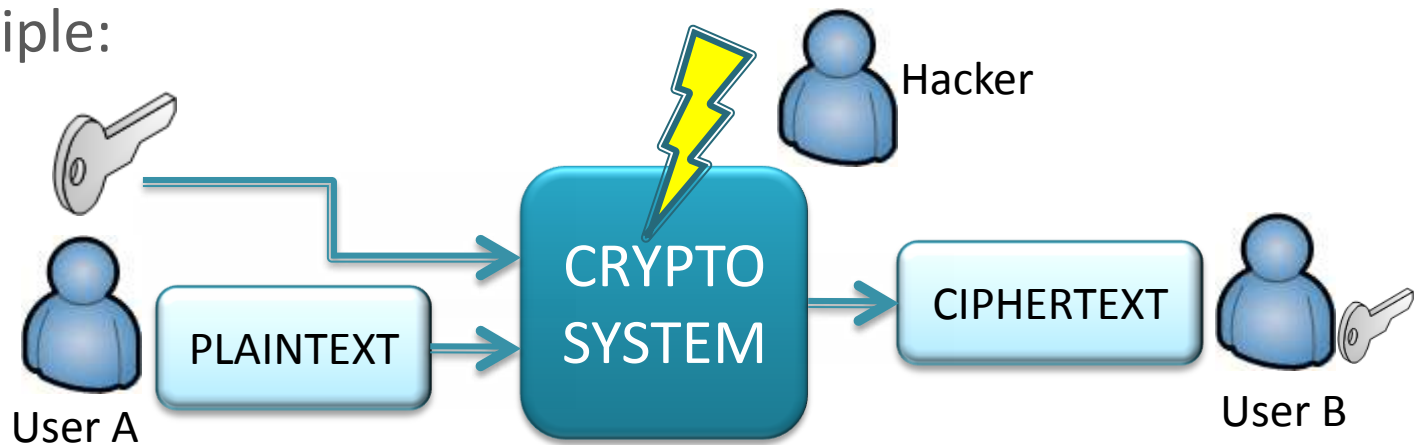
CEA Gardanne⁴

OUTLINE

- 1/ Introduction
 - Context of secure IC.
 - EM waves properties.
- 2/ EM injection Platform
 - Power Injection chain.
 - Illumination model.
- 3/ Experimental results
 - Injections on packaged IC.
 - Injections on unpackaged IC.
- 4/ Conclusion

CONTEXT: FAULT ATTACKS

- Principle:



- **Disturbing the crypto-computation to extract secret information.**

- Characteristics:

- Very efficient on unprotected systems.
- Unpredictable behavior.
- Complex to protect.

CONTEXT : ATTACKS VS COUNTERMEASURES

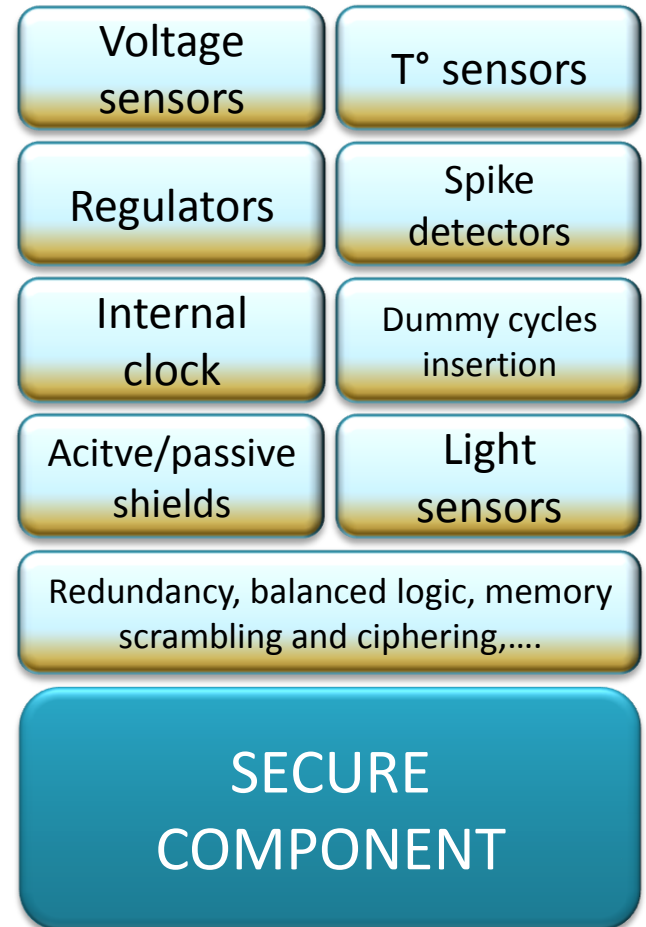
○ Global attacks:

- Operating limits(V, F, T°).
- Voltage spike.
- Clock glitch.

○ Local attacks:

- Laser shoot.

○ EM attack ?



○ EM potentials:

- *Penetration capabilities.*
- *Difficult to detect in electronic environment.*
- *Low-cost equipment.*

○ Feasibility of EM attacks?

- *Is it possible to create a local coupling with an IC?*
- *Is it possible to disturb an IC without removing the package?*

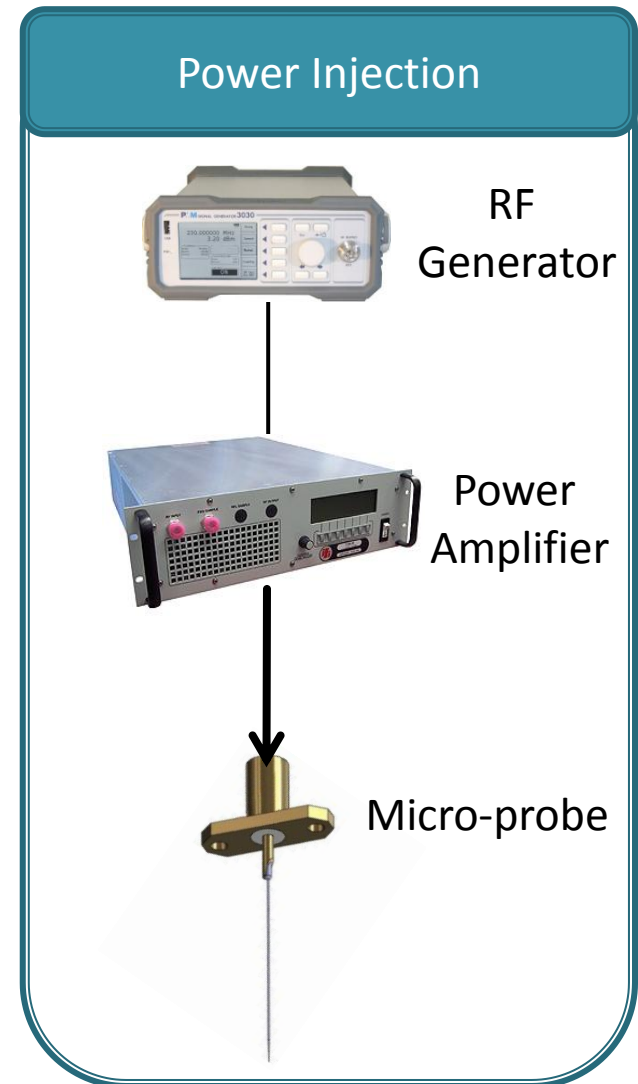
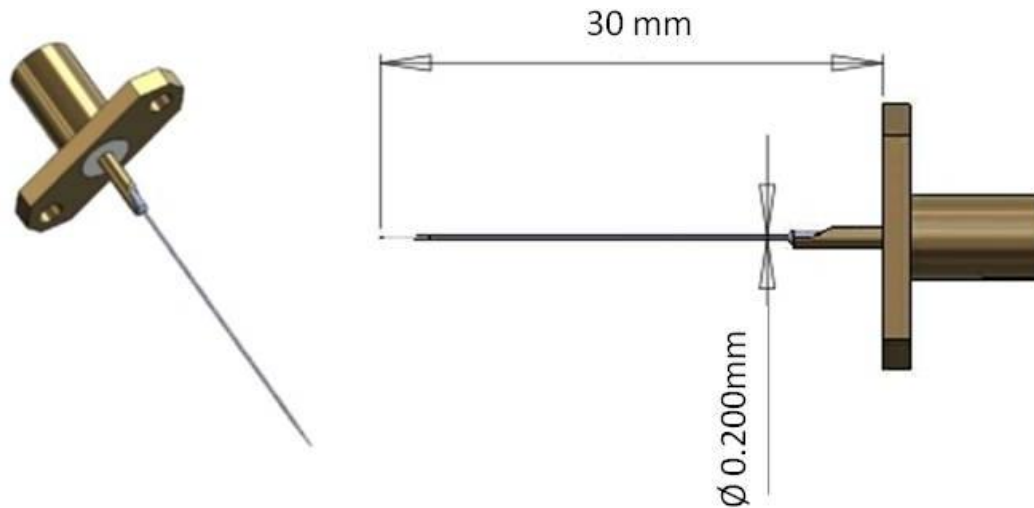
EM HARMONIC INJECTION



POWER INJECTION CHAIN

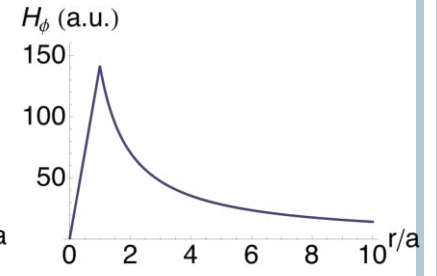
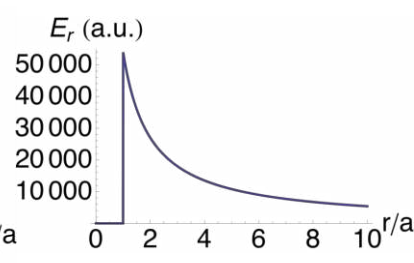
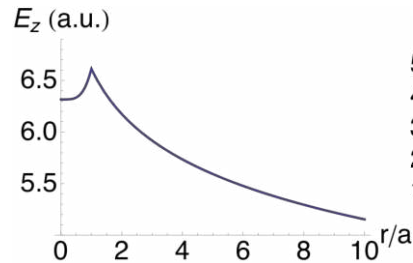
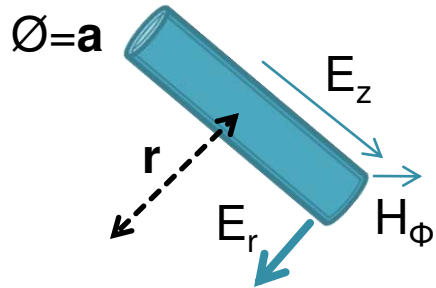
○ List of elements:

- RF generator.
- 50W power amplifier.
- RF cables.
- Micro-probe.

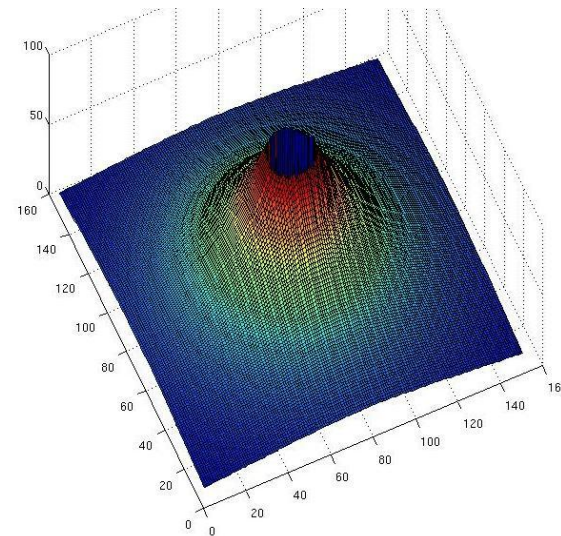
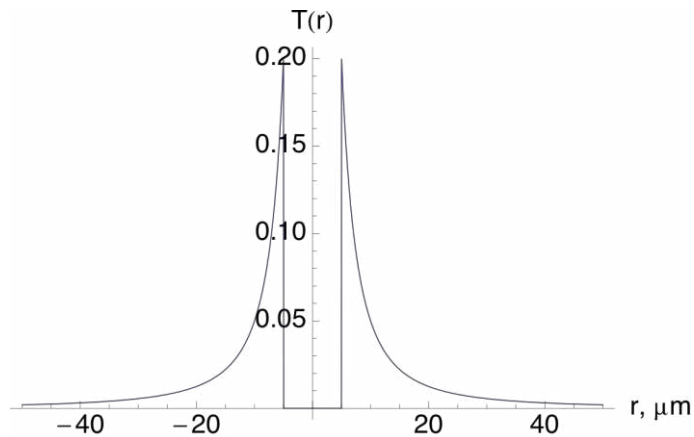


EM ILLUMINATION MODEL

EM fields:



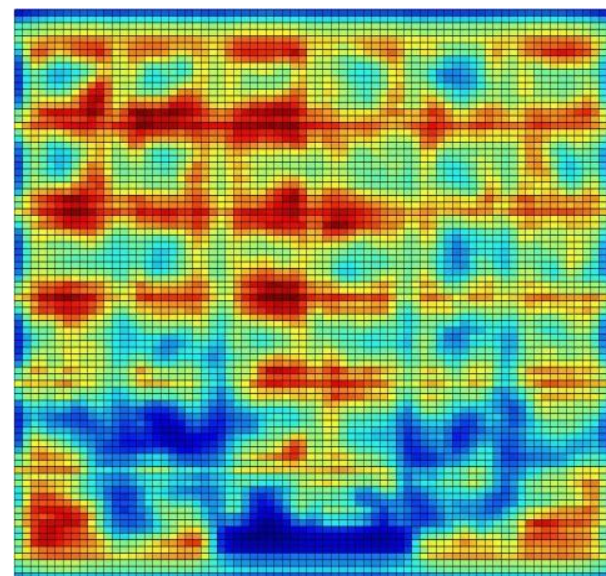
EM illumination:



- 90% of power in a ring of internal $\varnothing = 2 * a$ and external $\varnothing = 5 * a$.
- Local and intense EM injections.

EM COUPLING: IN BRIEF

- Our first works demonstrate the possibility of creating local EM couplings.
- The coupling depends on:
 - Probe position and geometry.
 - IC and receptive geometry pattern.
 - Frequency and power.



- ***“Local ElectroMagnetic Coupling with CMOS Integrated Circuits”***, F. Poucheret, B. Robisson, L. Chusseau, P. Maurine, *EMC-Compo 2011, Dubrovnik, Croatia.*

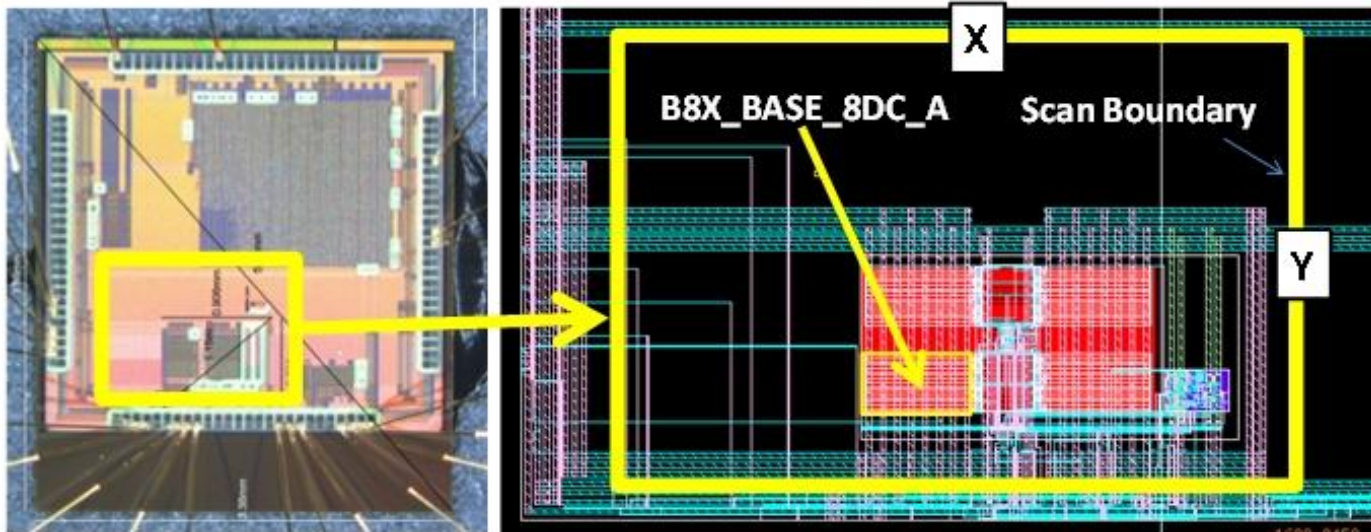
EXPERIMENTAL RESULTS



DUT: RING OSCILLATOR

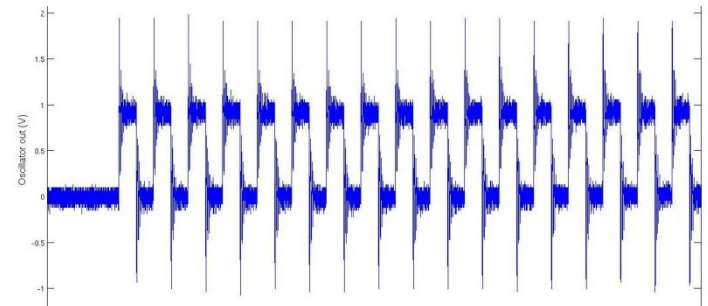
Choice of a Ring Oscillator:

- CMOS technology characterization.
- True Random Number Generator, Internal Clock Generator.

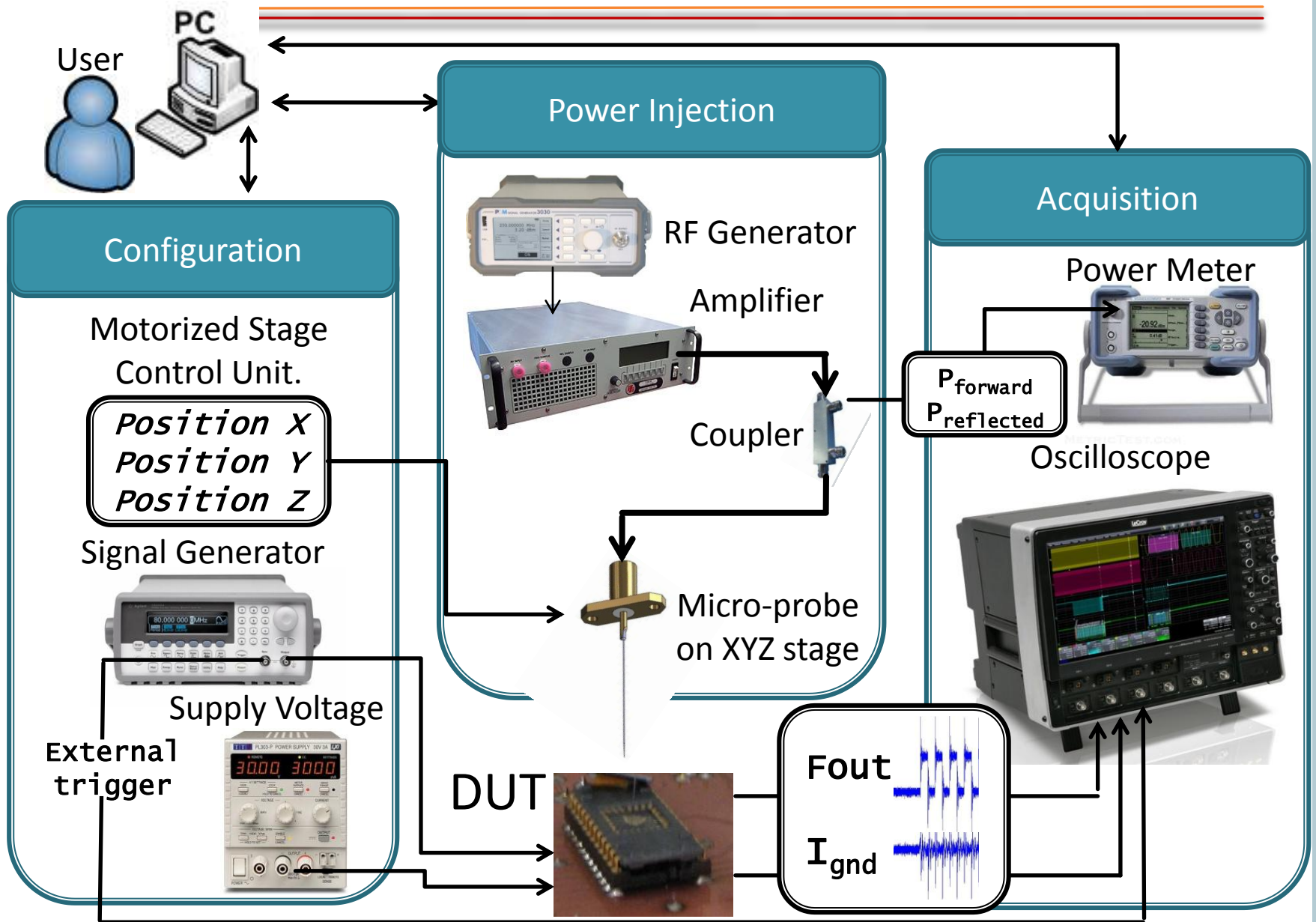


101 inverters + counter.

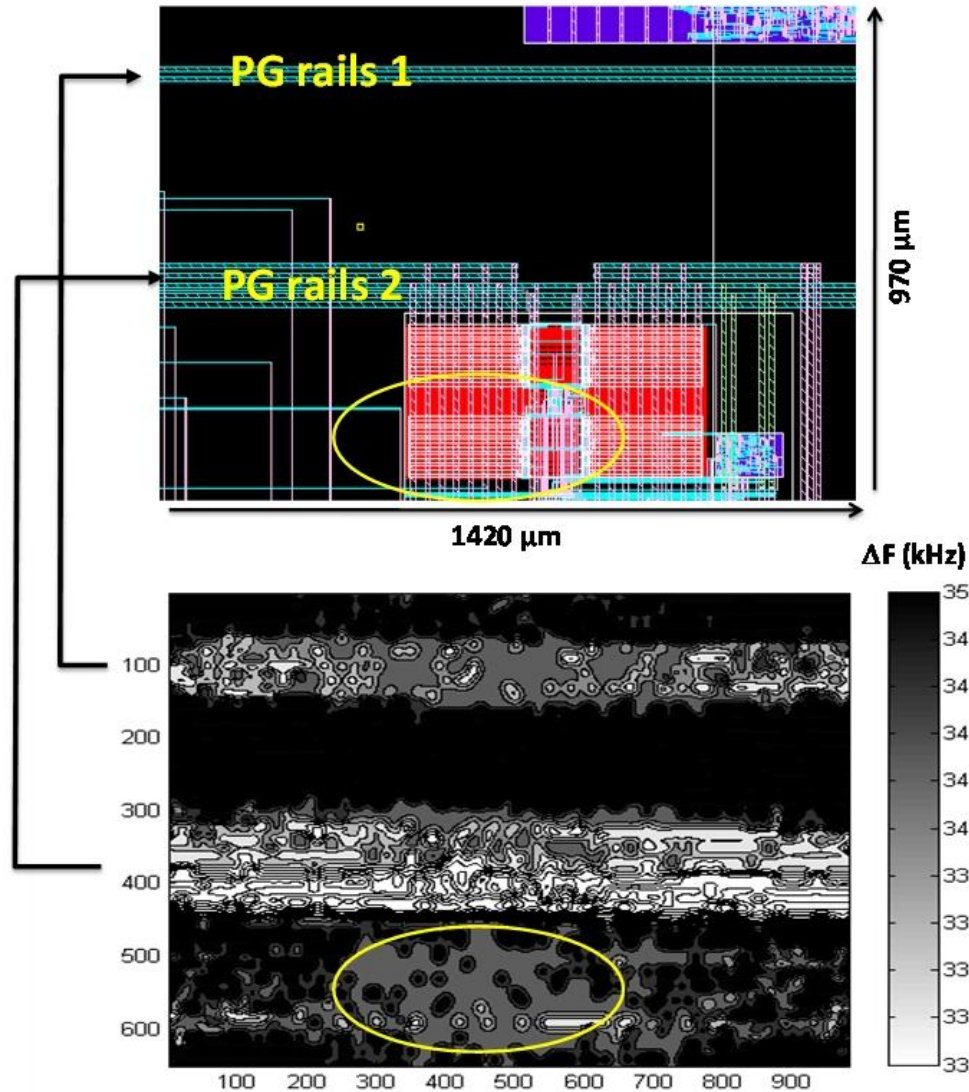
Output frequency (F_{out})=3.81MHz.



EXPERIMENTAL CONFIGURATION



ΔF CARTOGRAPHY ON UNPACKAGED IC



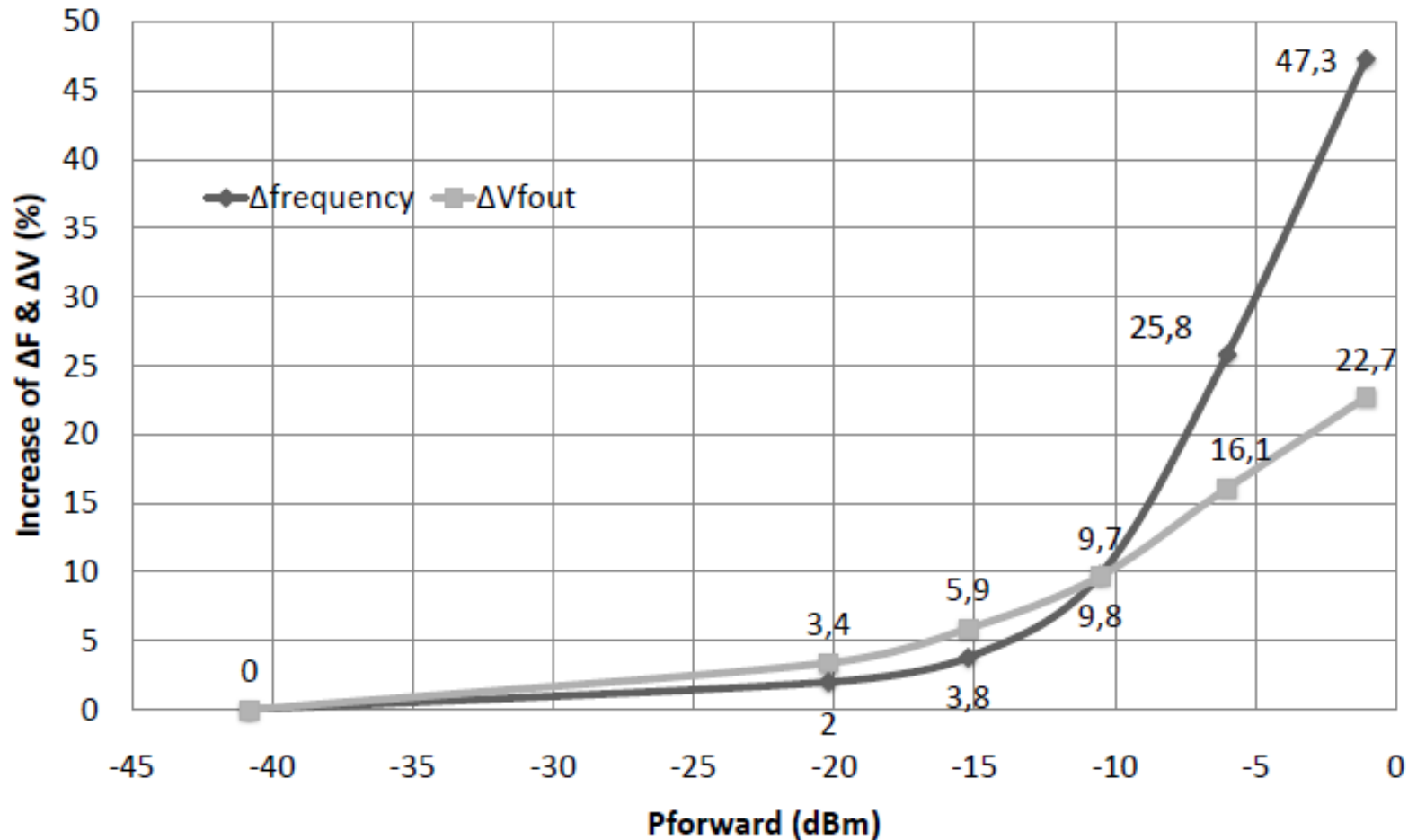
○ Parameters:

- 1GHz sine.
- $P_{\text{forward}} = 0.1\text{mW}$.
- Gap probe/IC = $50\mu\text{m}$.

○ Global increase of frequency: 350kHz (9.2%).

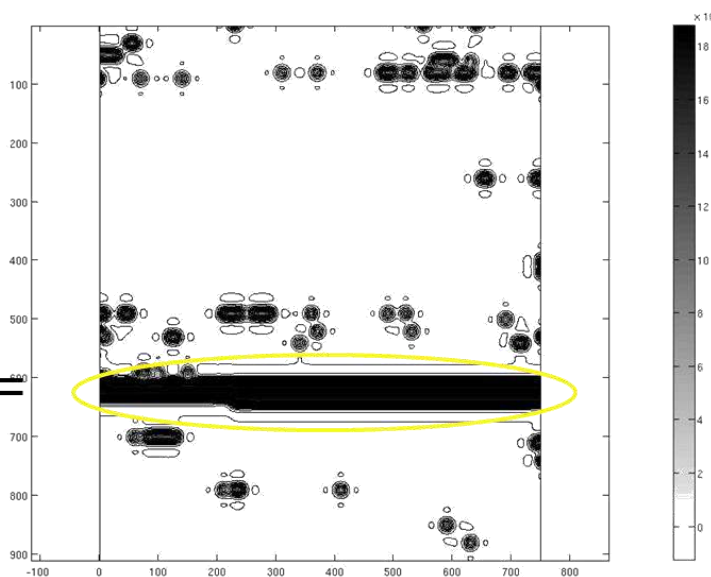
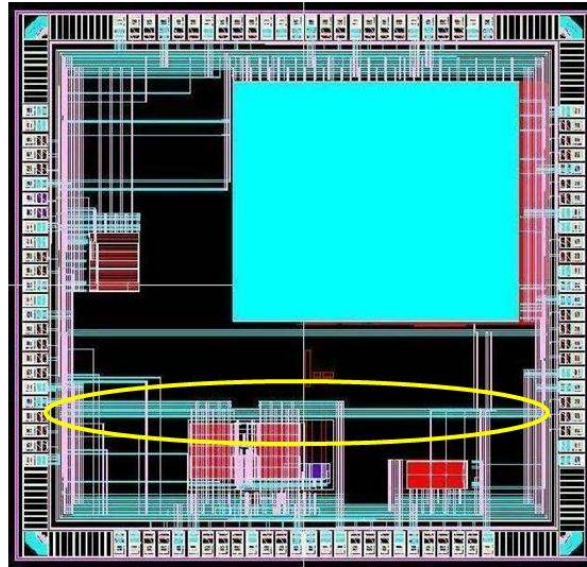
○ Local variations between 310-380kHz.

ΔF AND ΔV SWING EVOLUTIONS (PACKAGED IC).



- Increase of V_{dd} .
- Proportional to $P_{forward}$.

ΔF CARTOGRAPHY ON PACKAGED IC



Parameters:

- 1GHz sine.
- $P_{\text{forward}} = 6.63\text{mW}$.
- Gap probe/IC = 2mm.

- Local increase of 1.8 MHz (46,6%).
- Detection of patterns (width $\approx 100\mu\text{m}$).

CONCLUSION

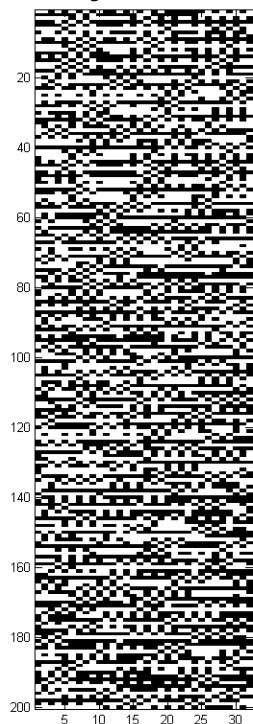
○ EM harmonic Injection into CMOS IC at High Frequency.

- Energy supply directly to power ground network.
- Contactless (several mm).
- Detection of 100 μ m wide patterns.

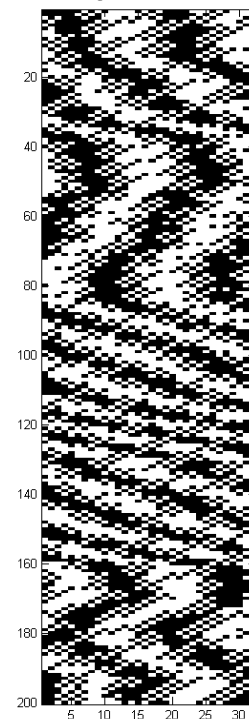
UNDERGOING WORK ON “WOLD” TRNG

- First EM Harmonic Injection into TRNG

Output stream without injection



Output stream with injection



- Modified bit stream at the output.
- Fail the statistical tests.